

KSC5338DTU Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	KSC5338DTU-DG
Manufacturer	onsemi
Manufacturer Product Number	KSC5338DTU
Description	TRANS NPN 450V 5A TO220-3
Detailed Description	Bipolar (BJT) Transistor NPN 450 V 5 A 11MHz 75 W Through Hole TO-220-3



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

KSC5338DTU

Series:

-

Transistor Type:

NPN

Voltage - Collector Emitter Breakdown (Max):

450 V

Current - Collector Cutoff (Max):

100 μ A

Power - Max:

75 W

Operating Temperature:

150°C (TJ)

Package / Case:

TO-220-3

Base Product Number:

KSC5338

Manufacturer:

onsemi

Product Status:

Last Time Buy

Current - Collector (Ic) (Max):

5 A

Vce Saturation (Max) @ Ib, Ic:

500mV @ 200mA, 1A

DC Current Gain (hFE) (Min) @ Ic, Vce:

6 @ 2A, 1V

Frequency - Transition:

11MHz

Mounting Type:

Through Hole

Supplier Device Package:

TO-220-3

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

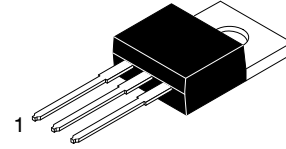
Not Applicable

ECCN:

EAR99

NPN Triple Diffused Planar Silicon Transistor

KSC5338D


TO-220-3LD
CASE 340AT

Features

- High Voltage Power Switch Switching Application
- Wide Safe Operating Area
- Built-in Free-Wheeling Diode
- Suitable for Electronic Ballast Application
- Small Variance in Storage Time
- Package Choice: TO-220
- This is a Pb-Free and a Halide Free Device

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	1000	V
V _{CEO}	Collector-Emitter Voltage	450	V
V _{EBO}	Emitter-Base Voltage	12	V
I _C	Collector Current (DC)	5	A
I _{CP}	Collector Current (Pulse) (Note 1)	10	A
I _B	Base Current (DC)	2	A
I _{BP}	Base Current (Pulse) (Note 1)	4	A
P _C	Power Dissipation (T _C = 25°C)	75	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 to 150	°C

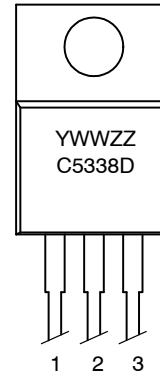
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle ≤ 10%

THERMAL CHARACTERISTICS

Symbol	Characteristic	Value	Unit	
R _{θjc}	Thermal Resistance	Junction to Case	1.65	°C/W
		Junction to Ambient	62.5	°C/W
T _L	Maximum Lead Temperature for Soldering	270	°C	

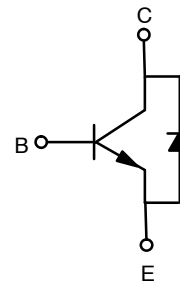
MARKING DIAGRAM



1. Base
2. Collector
3. Emitter

YWW = Date Code (Year and Week)
 ZZ = Lot Code
 C5338D = Specific Device Code

EQUIVALENT CIRCUIT



ORDERING INFORMATION

Device	Package	Shipping
KSC5338D	TO-220-3LD	1200 Units / Bulk
KSC5338DTU	(Pb-Free, Halide Free)	1000 Units / Tube

KSC5338D**ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units			
BV_{CBO}	Collector–Base Breakdown Voltage	$I_C = 1\text{ mA}, I_E = 0$	1000	–	–	V			
BV_{CEO}	Collector–Emitter Breakdown Voltage	$I_C = 5\text{ mA}, I_B = 0$	450	–	–	V			
BV_{EBO}	Emitter–Base Breakdown Voltage	$I_E = 1\text{ mA}, I_C = 0$	12	–	–	V			
I_{CBO}	Collector Cut-off Current	$V_{CB} = 800\text{ V}, I_E = 0$	–	–	10	μA			
I_{CES}	Collector Cut-off Current	$V_{CES} = 1000\text{ V}, I_{EB} = 0$	$T_a = 25^\circ\text{C}$	–	–	100	μA		
			$T_a = 125^\circ\text{C}$	–	–	500	μA		
I_{CEO}	Collector Cut-off Current	$V_{CE} = 450\text{ V}, I_B = 0$	$T_a = 25^\circ\text{C}$	–	–	100	μA		
			$T_a = 125^\circ\text{C}$	–	–	500	μA		
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 10\text{ V}, I_C = 0$	–	–	10	μA			
h_{FE}	DC Current Gain	$V_{CE} = 1\text{ V}, I_C = 0.8\text{ A}$	$T_a = 25^\circ\text{C}$	15	25	–			
			$T_a = 125^\circ\text{C}$	10	14	–			
		$V_{CE} = 1\text{ V}, I_C = 2\text{ A}$	$T_a = 25^\circ\text{C}$	6	9	–			
			$T_a = 125^\circ\text{C}$	4	6	–			
		$V_{CE} = 2.5\text{ V}, I_C = 1\text{ A}$	$T_a = 25^\circ\text{C}$	18	25	–			
			$T_a = 125^\circ\text{C}$	14	18	–			
$V_{CE(sat)}$	Collector–Emitter Saturation Voltage	$I_C = 0.8\text{ A}, I_B = 0.08\text{ A}$	$T_a = 25^\circ\text{C}$	–	0.35	0.5	V		
			$T_a = 125^\circ\text{C}$	–	0.55	0.75	V		
		$I_C = 2\text{ A}, I_B = 0.4\text{ A}$	$T_a = 25^\circ\text{C}$	–	0.47	0.75	V		
			$T_a = 125^\circ\text{C}$	–	0.9	1.1	V		
		$I_C = 0.8\text{ A}, I_B = 0.04\text{ A}$	$T_a = 25^\circ\text{C}$	–	0.9	1.5	V		
			$T_a = 125^\circ\text{C}$	–	1.8	2.5	V		
		$I_C = 1\text{ A}, I_B = 0.2\text{ A}$	$T_a = 25^\circ\text{C}$	–	0.22	0.5	V		
			$T_a = 125^\circ\text{C}$	–	0.3	0.6	V		
		$V_{BE(sat)}$	Base–Emitter Saturation Voltage	$I_C = 0.8\text{ A}, I_B = 0.08\text{ A}$	$T_a = 25^\circ\text{C}$	–	0.8	1.0	V
					$T_a = 125^\circ\text{C}$	–	0.65	0.9	V
$I_C = 2\text{ A}, I_B = 0.4\text{ A}$	$T_a = 25^\circ\text{C}$			–	0.9	1.0	V		
	$T_a = 125^\circ\text{C}$			–	0.8	0.9	V		
C_{ib}	Input Capacitance	$V_{EB} = 10\text{ V}, I_C = 0.5\text{ A}, f = 1\text{ MHz}$	–	550	750	pF			
C_{ob}	Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	–	60	100	pF			
f_T	Current Gain Bandwidth Product	$I_C = 0.5\text{ A}, V_{CE} = 10\text{ V}$	–	11	–	MHz			
V_F	Diode Forward Voltage	$I_F = 1\text{ A}, I_C = 1\text{ mA}, I_E = 0$	$T_a = 25^\circ\text{C}$	–	0.86	1.3	V		
			$T_a = 125^\circ\text{C}$	–	0.79	–	V		
		$I_F = 2\text{ A}$	$T_a = 25^\circ\text{C}$	–	0.95	1.5	V		
			$T_a = 125^\circ\text{C}$	–	0.88	–	V		
t_{fr}	Diode Forward Recovery Time ($di/dt = 10\text{ A}/\mu\text{s}$)	$I_F = 0.4\text{ A}$	–	460	–	ns			
		$I_F = 1\text{ A}$	–	360	–				
		$I_F = 2\text{ A}$	–	325	–				
$V_{CE(DSAT)}$	Dynamic Saturation Voltage	$I_C = 1\text{ A}, I_{B1} = 100\text{ mA}$ $V_{CC} = 300\text{ V}$ at $1\text{ }\mu\text{s}$	$T_a = 25^\circ\text{C}$	–	8	–	V		
			$T_a = 125^\circ\text{C}$	–	15	–	V		
		$I_C = 1\text{ A}, I_{B1} = 100\text{ mA}$ $V_{CC} = 300\text{ V}$ at $3\text{ }\mu\text{s}$	$T_a = 25^\circ\text{C}$	–	2.9	–	V		
			$T_a = 125^\circ\text{C}$	–	8	–	V		
		$I_C = 2\text{ A}, I_{B1} = 400\text{ mA}$ $V_{CC} = 300\text{ V}$ at $1\text{ }\mu\text{s}$	$T_a = 25^\circ\text{C}$	–	9	–	V		
			$T_a = 125^\circ\text{C}$	–	17	–	V		
		$I_C = 2\text{ A}, I_{B1} = 400\text{ mA}$ $V_{CC} = 300\text{ V}$ at $3\text{ }\mu\text{s}$	$T_a = 25^\circ\text{C}$	–	1.9	–	V		
			$T_a = 125^\circ\text{C}$	–	8.5	–	V		

KSC5338D**ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units	
RESISTIVE LOAD SWITCHING (D.C. \leq 10%, Pulse Width = 40 μs)							
t_{ON}	Turn On Time	$I_C = 2.5 \text{ A}, I_{B1} = 500 \text{ mA},$ $I_{B2} = -1 \text{ A}, V_{CC} = 250 \text{ V}, R_L = 100 \Omega$	–	500	750	ns	
t_{STG}	Storage Time		1.2	–	1.5	μs	
t_F	Fall Time		–	100	200	ns	
t_{ON}	Turn On Time	$I_C = 2 \text{ A}, I_{B1} = 400 \text{ mA},$ $I_{B2} = -1 \text{ A}, V_{CC} = 300 \text{ V},$ $R_L = 150 \Omega$	$T_a = 25^\circ\text{C}$	–	100	150	ns
			$T_a = 125^\circ\text{C}$	–	150	–	ns
t_{STG}	Storage Time		$T_a = 25^\circ\text{C}$	–	1.4	2.2	μs
			$T_a = 125^\circ\text{C}$	–	1.7	–	μs
t_F	Fall Time		$T_a = 25^\circ\text{C}$	–	90	150	ns
			$T_a = 125^\circ\text{C}$	–	150	–	ns
t_{ON}	Turn On Time	$I_C = 2.5 \text{ A}, I_{B1} = 500 \text{ mA},$ $I_{B2} = -5 \text{ mA}, V_{CC} = 300 \text{ V},$ $R_L = 120 \Omega$	$T_a = 25^\circ\text{C}$	–	120	150	ns
			$T_a = 125^\circ\text{C}$	–	150	–	ns
t_{STG}	Storage Time		$T_a = 25^\circ\text{C}$	1.8	–	2.1	μs
			$T_a = 125^\circ\text{C}$	–	2.6	–	μs
t_F	Fall Time		$T_a = 25^\circ\text{C}$	–	110	150	ns
			$T_a = 125^\circ\text{C}$	–	160	–	ns

INDUCTIVE LOAD SWITCHING ($V_{CC} = 15 \text{ V}$)

t_{STG}	Storage Time	$I_C = 2.5 \text{ A}, I_{B1} = 500 \text{ mA},$ $I_{B2} = -0.5 \text{ A}, V_Z = 350 \text{ V},$ $L_C = 300 \mu\text{H}$	$T_a = 25^\circ\text{C}$	–	1.9	2.2	μs
			$T_a = 125^\circ\text{C}$	–	2.4	–	μs
t_F	Fall Time	$I_C = 2 \text{ A}, I_{B1} = 400 \text{ mA},$ $I_{B2} = -0.4 \text{ A}, V_Z = 300 \text{ V},$ $L_C = 200 \mu\text{H}$	$T_a = 25^\circ\text{C}$	–	160	200	ns
			$T_a = 125^\circ\text{C}$	–	330	–	ns
t_C	Cross-over Time		$T_a = 25^\circ\text{C}$	–	350	500	ns
			$T_a = 125^\circ\text{C}$	–	750	–	ns
t_{STG}	Storage Time	$I_C = 1 \text{ A}, I_{B1} = 100 \text{ mA},$ $I_{B2} = -0.5 \text{ A}, V_Z = 300 \text{ V},$ $L_C = 200 \mu\text{H}$	$T_a = 25^\circ\text{C}$	1.95	–	2.25	μs
			$T_a = 125^\circ\text{C}$	–	2.9	–	μs
t_F	Fall Time		$T_a = 25^\circ\text{C}$	–	120	150	ns
			$T_a = 125^\circ\text{C}$	–	270	–	ns
t_C	Cross-over Time		$T_a = 25^\circ\text{C}$	–	300	450	ns
			$T_a = 125^\circ\text{C}$	–	700	–	ns
t_{STG}	Storage Time	$I_C = 1 \text{ A}, I_{B1} = 100 \text{ mA},$ $I_{B2} = -0.5 \text{ A}, V_Z = 300 \text{ V},$ $L_C = 200 \mu\text{H}$	$T_a = 25^\circ\text{C}$	–	0.6	0.8	μs
			$T_a = 125^\circ\text{C}$	–	1.0	–	μs
t_F	Fall Time		$T_a = 25^\circ\text{C}$	–	70	–	ns
			$T_a = 125^\circ\text{C}$	–	110	–	ns
t_C	Cross-over Time	$I_C = 1 \text{ A}, I_{B1} = 100 \text{ mA},$ $I_{B2} = -0.5 \text{ A}, V_Z = 300 \text{ V},$ $L_C = 200 \mu\text{H}$	$T_a = 25^\circ\text{C}$	–	80	130	ns
			$T_a = 125^\circ\text{C}$	–	170	–	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

KSC5338D

TYPICAL CHARACTERISTICS

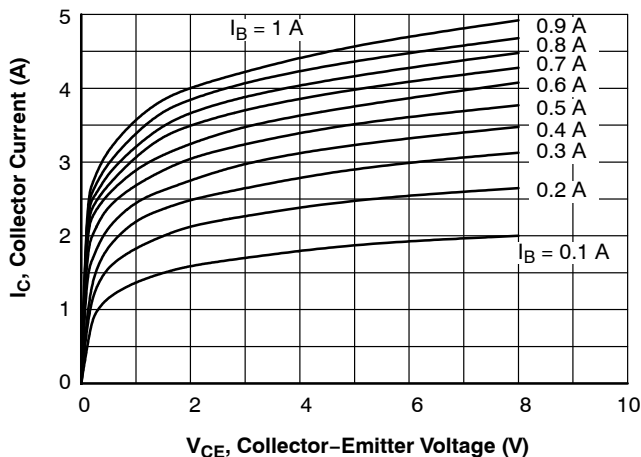


Figure 1. Static Characteristic

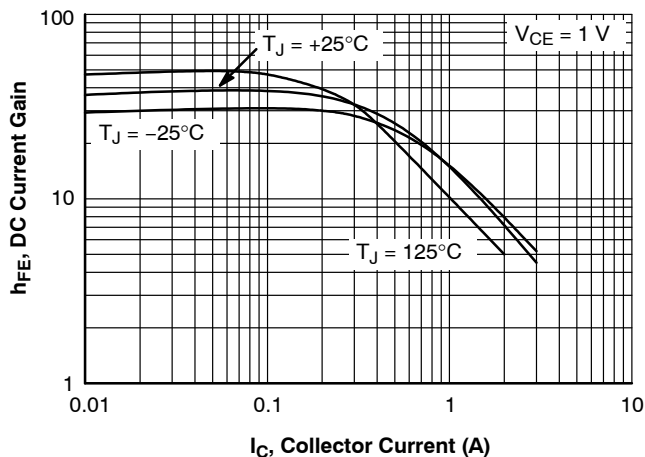


Figure 2. DC Current Gain

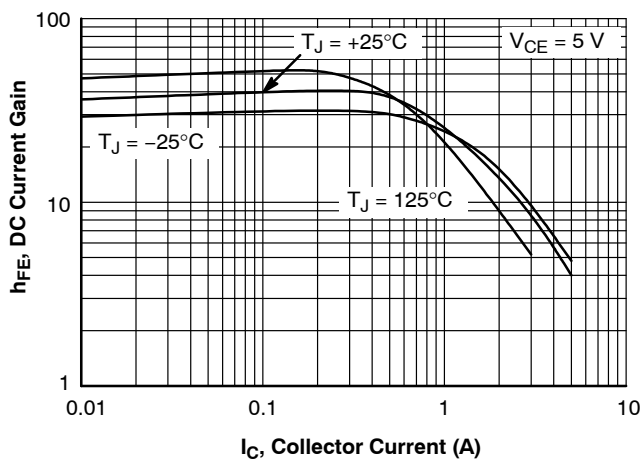


Figure 3. DC Current Gain

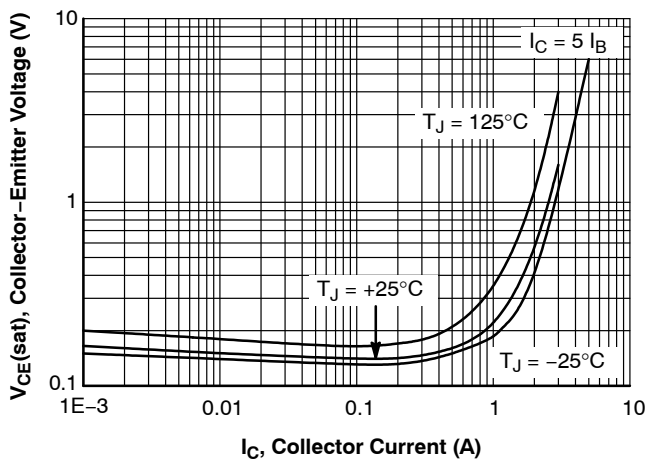


Figure 4. Collector-Emitter Saturation Voltage

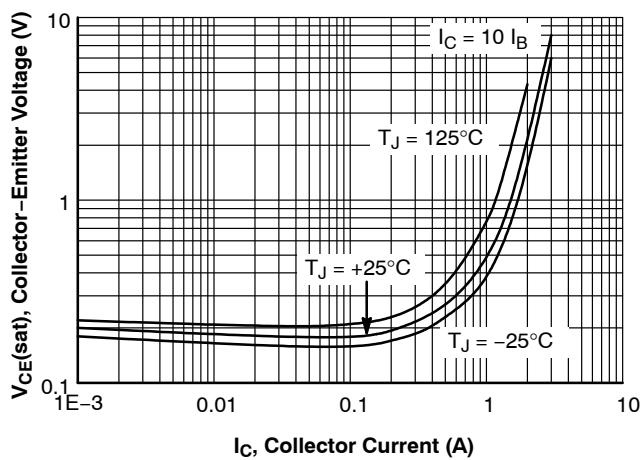


Figure 5. Collector-Emitter Saturation Voltage

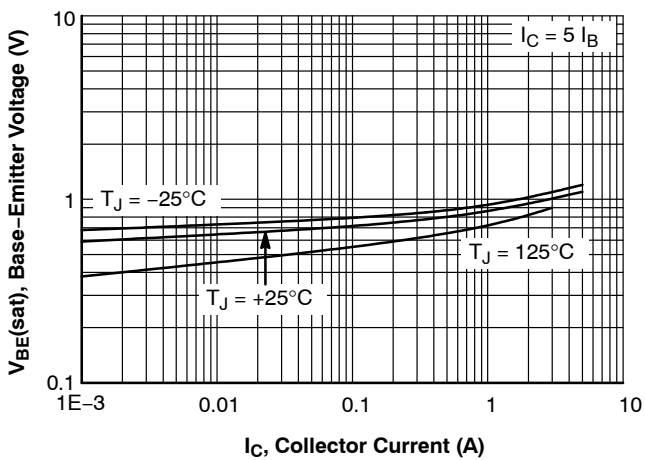


Figure 6. Base-Emitter Saturation Voltage

KSC5338D

TYPICAL CHARACTERISTICS (continued)

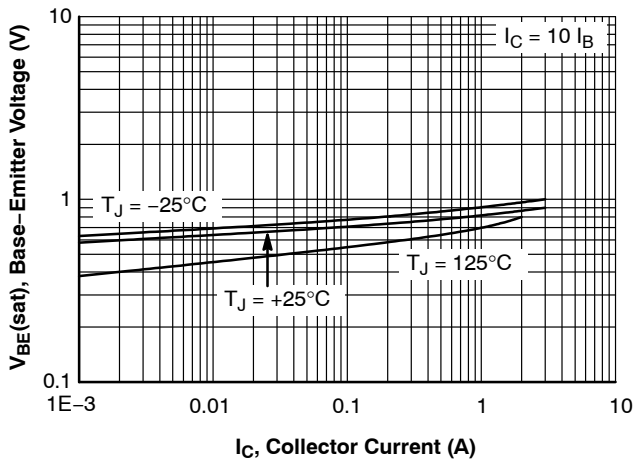


Figure 7. Base-Emitter Saturation Voltage

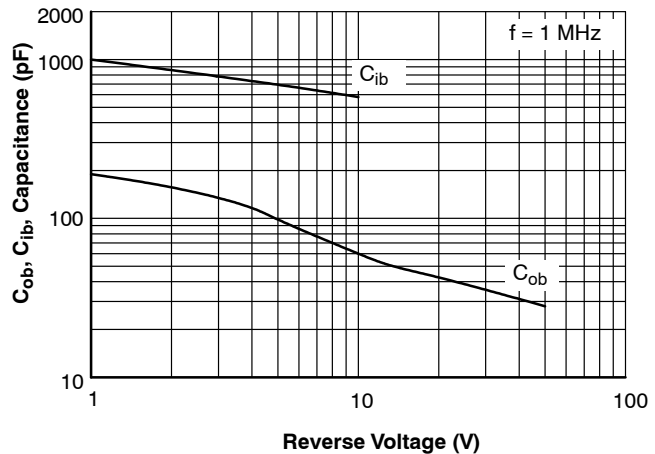


Figure 8. Collector Output Capacitance

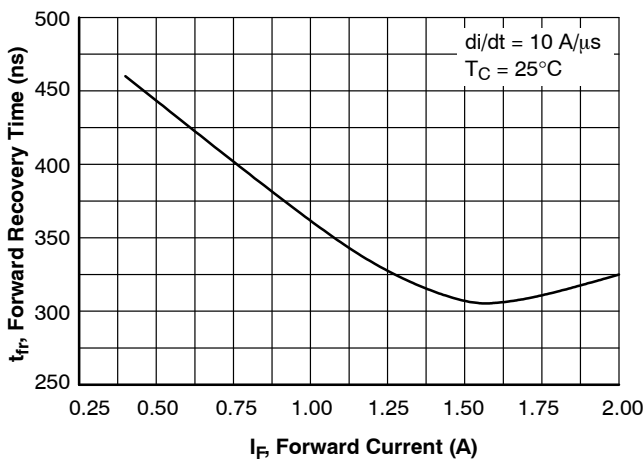


Figure 9. Forward Recovery Time

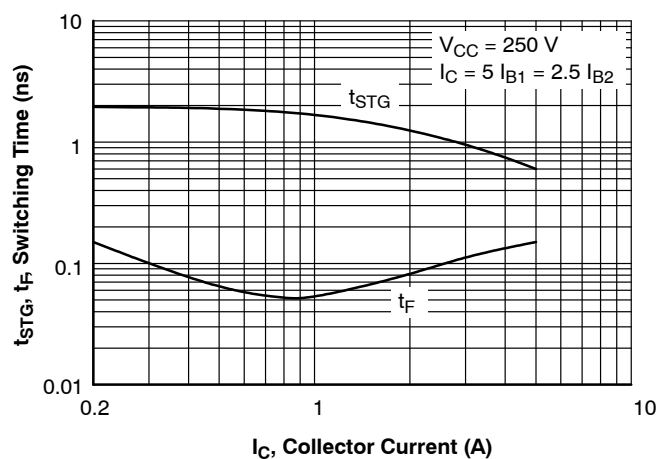


Figure 10. Switching Time

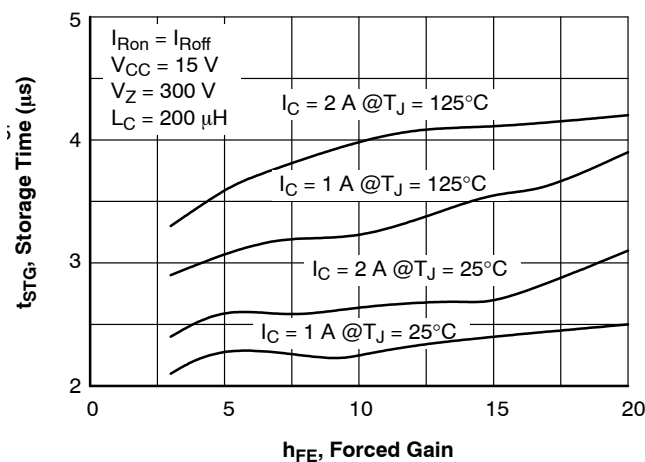


Figure 11. Induction Storage Time

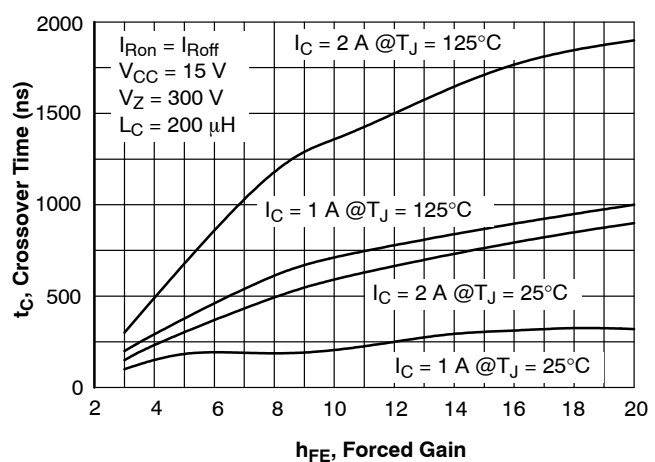


Figure 12. Inductive Crossover Time

KSC5338D

TYPICAL CHARACTERISTICS (continued)

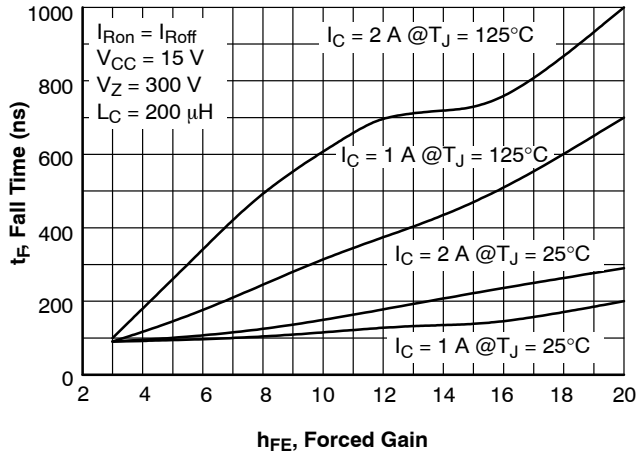


Figure 13. Inductive Fall Time

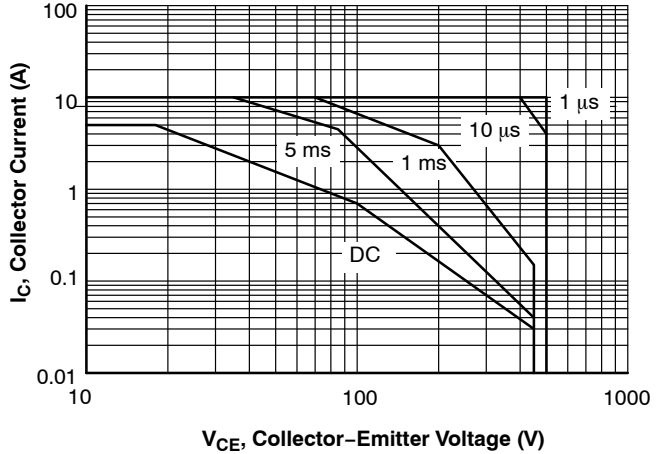


Figure 14. Safe Operating Area

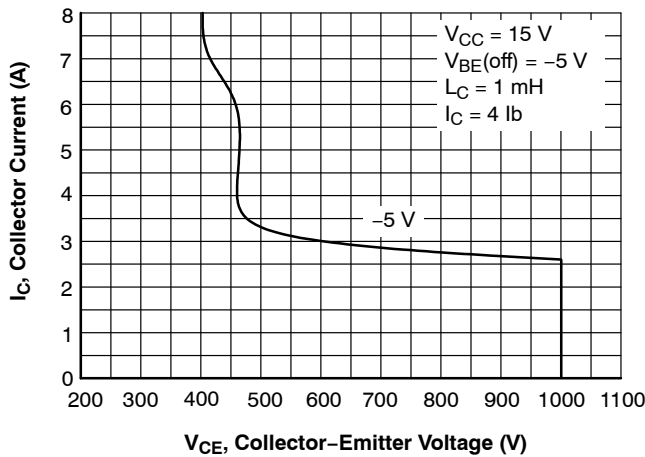


Figure 15. Reverse Bias Safe Operating

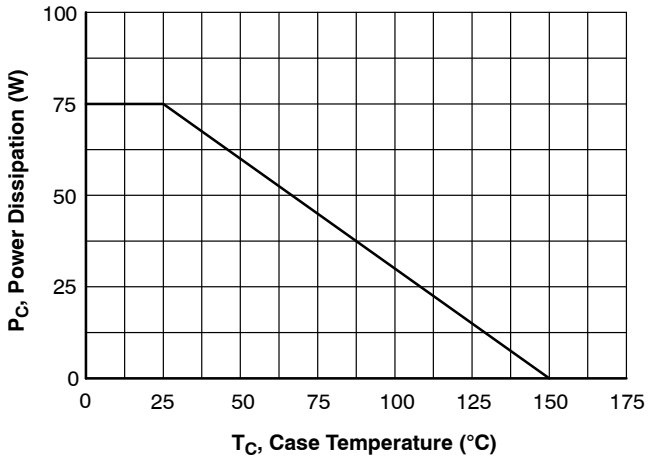


Figure 16. Power Derating

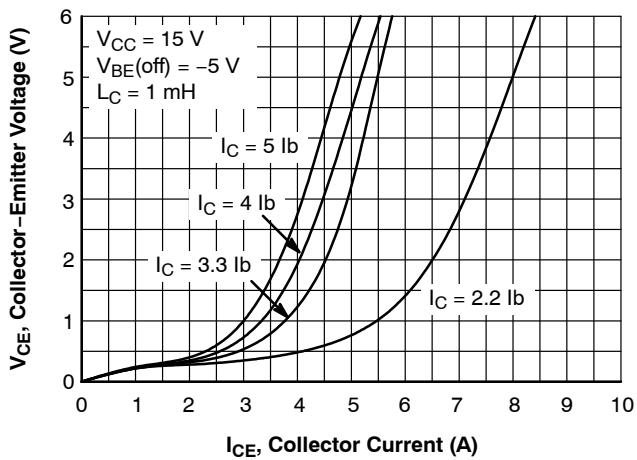
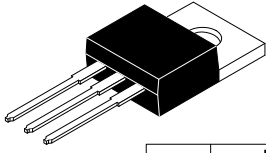


Figure 17. RBSOA Saturation


TO-220-3LD
CASE 340AT
ISSUE B

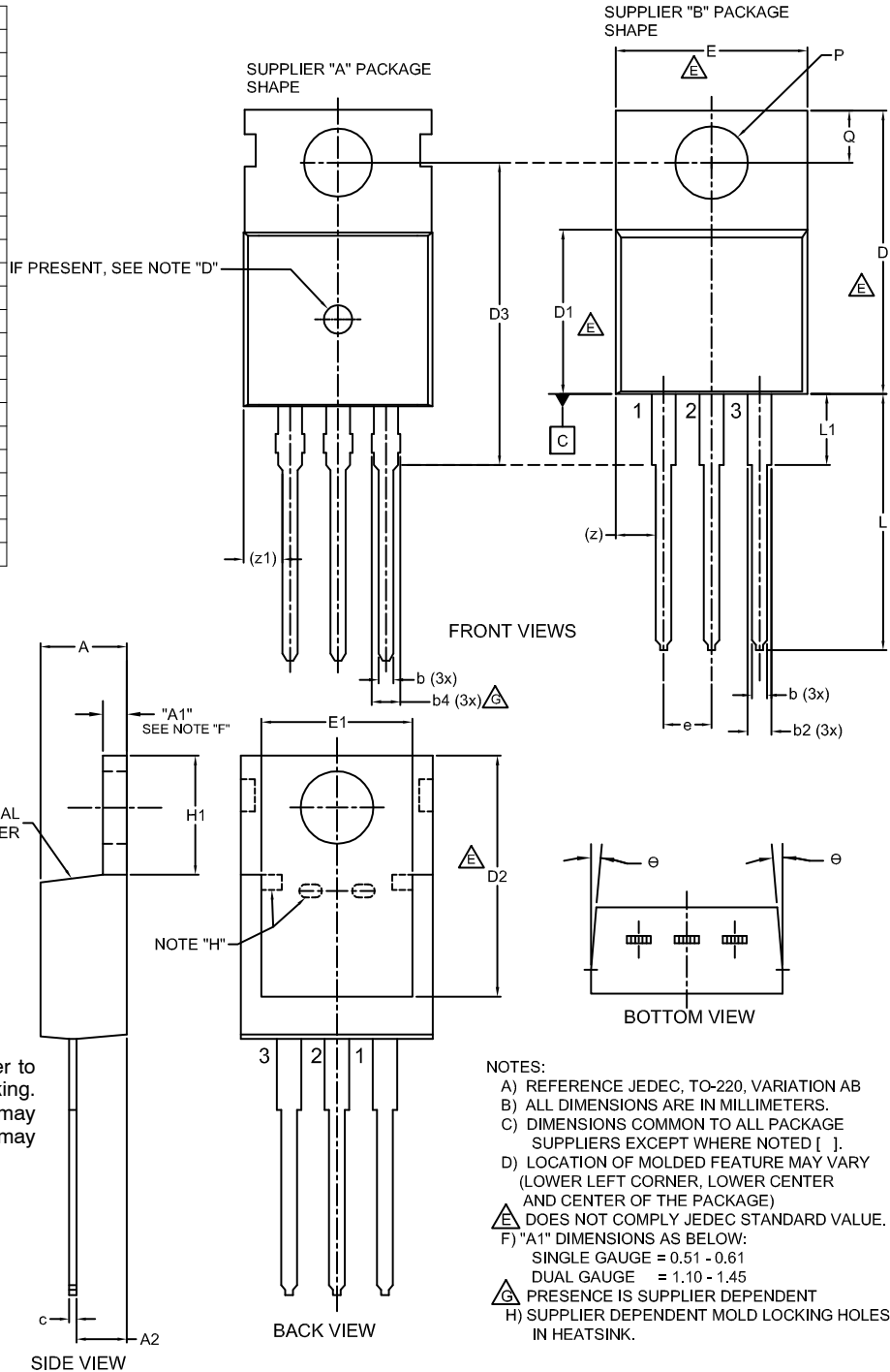
DATE 08 AUG 2022

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	4.00	--	4.70
A1	SEE NOTE "F"		
A2	2.10	--	2.85
b	0.55	--	1.00
b2	1.10	--	1.62
b4	1.42	--	1.62
c	0.36	--	0.60
D	13.90	--	16.30
D1	8.13	--	9.40
D2	11.50	--	14.30
D3	15.42	--	16.51
E	9.65	--	10.67
E1	7.59	--	8.65
e	2.40	--	2.67
H1	6.06	--	6.69
L	12.70	--	14.04
L1	2.70	--	4.10
P	3.50	--	4.00
Q	2.50	--	3.40
z	2.13 REF		
z1	2.06 REF		
θ	3°	--	5°

GENERIC MARKING DIAGRAM*


XXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.


NOTES:

- A) REFERENCE JEDEC, TO-220, VARIATION AB
 B) ALL DIMENSIONS ARE IN MILLIMETERS.
 C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [].
 D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
 ⚠ DOES NOT COMPLY JEDEC STANDARD VALUE.
 F) "A1" DIMENSIONS AS BELOW:
 SINGLE GAUGE = 0.51 - 0.61
 DUAL GAUGE = 1.10 - 1.45
 ⚠ PRESENCE IS SUPPLIER DEPENDENT
 H) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.

DOCUMENT NUMBER:	98AON13818G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TO-220-3LD	PAGE 1 OF 1

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

OUR CERTIFICATE

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we stricly control the quality of products and services. Welcome your RFQ to

Email: Info@DiGi-Electronics.com



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.